

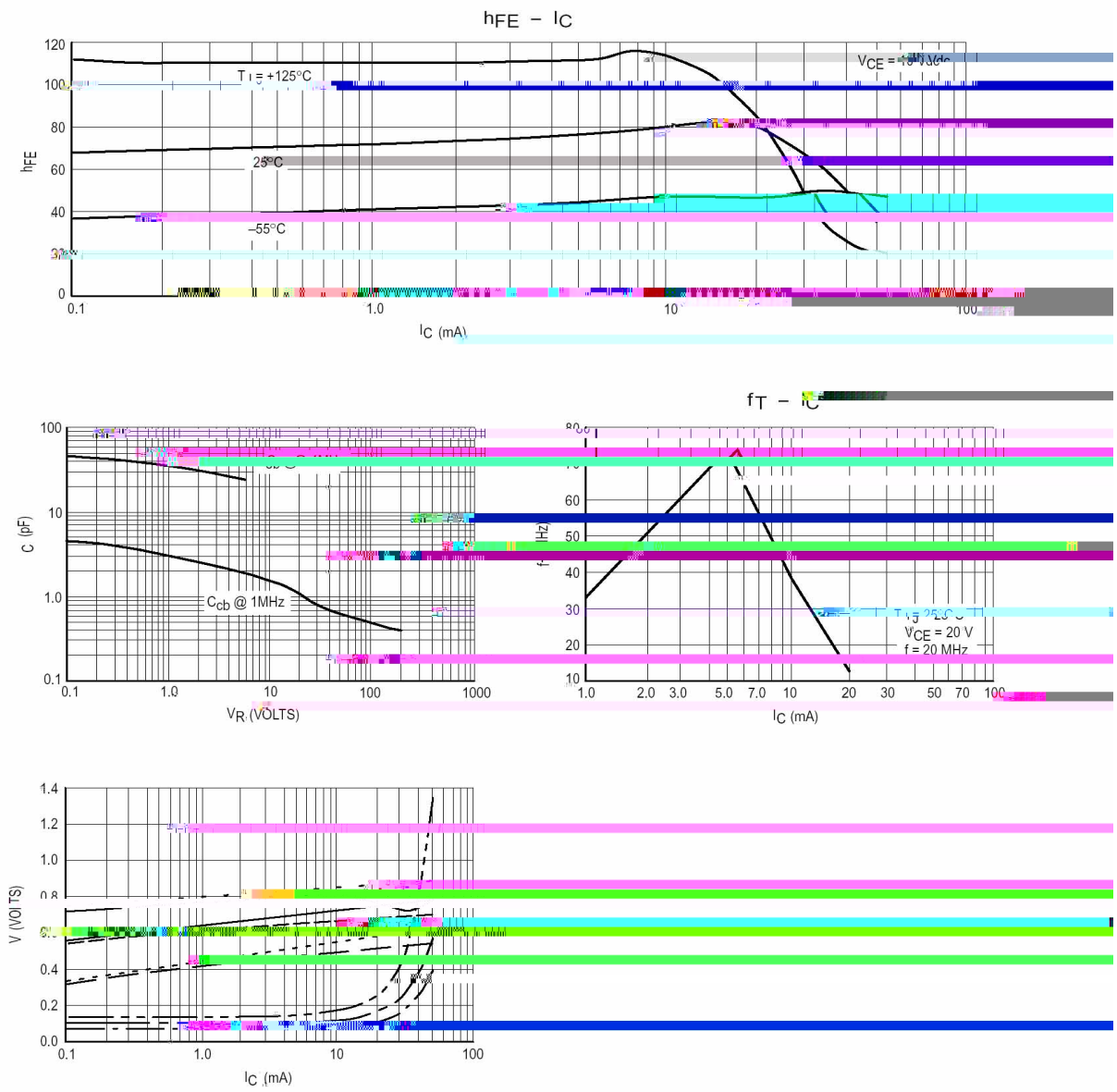
Silicon NPN transistor in a TO-92 Plastic Package.

High voltage, low saturation, low  $C_{cb}$ .

High voltage control circuit.

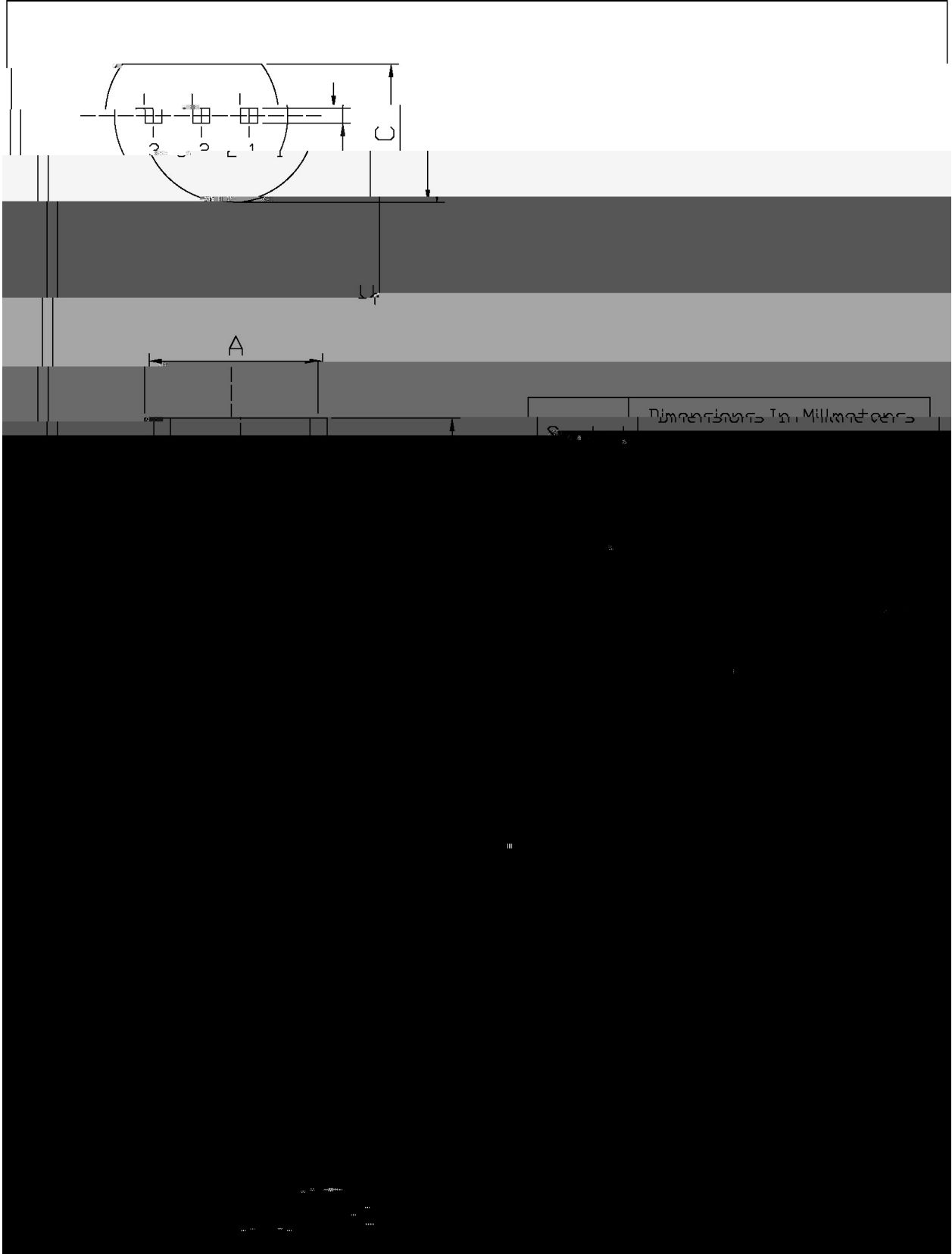
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	$V_{CBO}$	200	V
Collector to Emitter Voltage	$V_{CEO}$	200	V
Emitter to Base Voltage	$V_{EBO}$	6.0	V
Collector Current - Continuous	$I_C$	500	mA
Collector Power Dissipation	$P_C$	625	mW
Junction Temperature	$T_j$	150	
Storage Temperature Range	$T_{stg}$	-55 150	

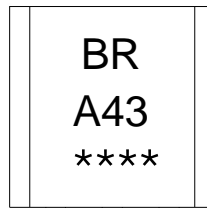
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	$V_{CBO}$	$I_C=100\mu A$ $I_E=0$	200			V
Collector to Emitter Breakdown Voltage	$V_{CEO}$	$I_C=1.0mA$ $I_B=0$	200			V
Emitter to Base Breakdown Voltage	$V_{EBO}$	$I_E=100\mu A$ $I_C=0$	6.0			V
Collector Cut-Off Current	$I_{CBO}$	$V_{CB}=160V$ $I_E=0$			0.1	$\mu A$
Emitter Cut-Off Current	$I_{EBO}$	$V_{EB}=4.0V$ $I_C=0$			0.1	$\mu A$
DC Current Gain	$h_{FE(1)}$	$V_{CE}=10V$ $I_C=10mA$	40			
	$h_{FE(2)}$	$V_{CE}=10V$ $I_C=30mA$	40			
	$h_{FE(3)}$	$V_{CE}=10V$ $I_C=1.0mA$	25			
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=20mA$ $I_B=2.0mA$			0.5	V
Base to Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=20mA$ $I_B=2.0mA$			0.9	V
Transition Frequency	$f_T$	$V_{CE}=20V$ $f=100MHz$ $I_C=10mA$	50			MHz
Output Capacitance	$C_{ob}$	$V_{CB}=20V$ $f=1.0MHz$ $I_E=0$			4.0	pF



T0-92

Unit: mm





Note:

BR: Company Code.

A43: Product Type.

\*\*\*\*: Lot No. Code,code change with Lot No.

